



MMDT3904

DUAL NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

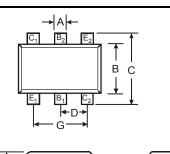
-55 to +150

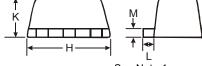
Features

- **Epitaxial Planar Die Construction**
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 3)
- "Green" Device (Note 4 and 5)

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Terminals: Lead bearing terminal plating available. See Ordering information Page 3
- Marking Information: KAP, See Page 3
- Ordering Information: See Page 3
- Weight: 0.003 grams (approximate)







SOT-563								
Dim	Min	Max	Тур					
Α	0.15	0.30	0.25					
В	1.10	1.25	1.20					
С	1.55 1.70 1.60							
D	0.50							
G	0.90	1.10	1.00					
Н	1.50	1.60						
к	0.56	0.60	0.60					
L	0.10	0.30	0.20					
м	0.10	0.18	0.11					
All I	All Dimensions in mm							

Maximum Ratings @T _A = 25°C unless otherwise specified								
Characteristic	Symbol	Value	Unit					
Collector-Base Voltage	V _{CBO}	60	V					
Collector-Emitter Voltage	V _{CEO}	40	V					
Emitter-Base Voltage	V _{EBO}	6.0	V					
Collector Current - Continuous	Ic	200	mA					
Power Dissipation (Note 2)	Pd	200	mW					
Thermal Resistance, Junction to Ambient	Rela	625	°C/W					

1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

Package is holi-polarized. Parts hay be on recent orientation modulated, not rotated, or model (continue).
Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

Tj, T_{STG}

3. No purposefully added lead.

Operating and Storage Temperature Range

Notes:

4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date 5. Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

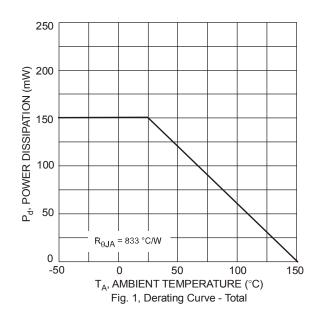
°C

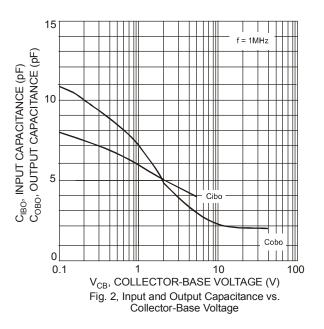


Electrical Characteristics @T_A = 25°C unless otherwise specified

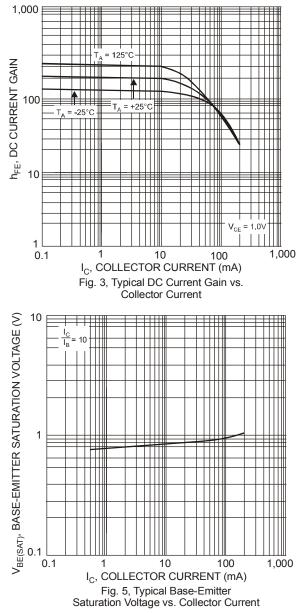
Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60	_	V	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$	
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40		V	I _C = 1.0mA, I _B = 0	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5.0	_	V	$I_{E} = 10 \mu A, I_{C} = 0$	
Collector Cutoff Current	ICEX	_	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V	
Base Cutoff Current	I _{BL}	_	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V	
ON CHARACTERISTICS (Note 6)	•					
DC Current Gain	h _{FE}	40 70 100 60 30	 300 	_	$\begin{split} I_{C} &= 100 \mu A, V_{CE} = 1.0 V \\ I_{C} &= 1.0 m A, V_{CE} = 1.0 V \\ I_{C} &= 10 m A, V_{CE} = 1.0 V \\ I_{C} &= 50 m A, V_{CE} = 1.0 V \\ I_{C} &= 100 m A, V_{CE} = 1.0 V \end{split}$	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.20 0.30	V	$I_{C} = 10mA, I_{B} = 1.0mA$ $I_{C} = 50mA, I_{B} = 5.0mA$	
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65	0.85 0.95	V	I_{C} = 10mA, I_{B} = 1.0mA I_{C} = 50mA, I_{B} = 5.0mA	
SMALL SIGNAL CHARACTERISTICS				_	-	
Output Capacitance	C _{obo}	_	4.0	pF	V_{CB} = 5.0V, f = 1.0MHz, I _E = 0	
nput Capacitance	Cibo	_	8.0	pF	V_{EB} = 0.5V, f = 1.0MHz, I _C = 0	
nput Impedance	h _{ie}	1.0	10	kΩ		
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1.0mA,	
Small Signal Current Gain	h _{fe}	100	400	—	f = 1.0kHz	
Output Admittance	h _{oe}	1.0	40	μS		
Current Gain-Bandwidth Product	f⊤	300	—	MHz	V _{CE} = 20V, I _C = 10mA, f = 100MHz	
Noise Figure	NF	_	5.0	dB	V _{CE} = 5.0V, I _C = 100μA, R _S = 1.0kΩ, f = 1.0kHz	
SWITCHING CHARACTERISTICS	•		·	•		
Delay Time	t _d	_	35	ns	V _{CC} = 3.0V, I _C = 10mA,	
Rise Time	tr		35	ns	V _{BE(off)} = - 0.5V, I _{B1} = 1.0mA	
Storage Time	ts		200	ns	V _{CC} = 3.0V, I _C = 10mA,	
all Time	t _f		50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$	

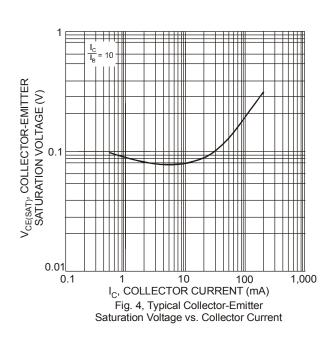
Notes: 6. Short duration pulse test used to minimize self-heating effect.











Ordering Information (Note 7)

Device	Packaging	Shipping
MMDT3904V-7	SOT-563	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

ate Code Key				<u> П [</u> кар үм	Y Y	M = Date = Year (e	Code Mar x: R = 20		ode			
Year	2004	20	05	2006	2007	20	08	2009	2010	20	011	2012
Code	R	5	\$	Т	. U		V	W	Х		Y	Z
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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